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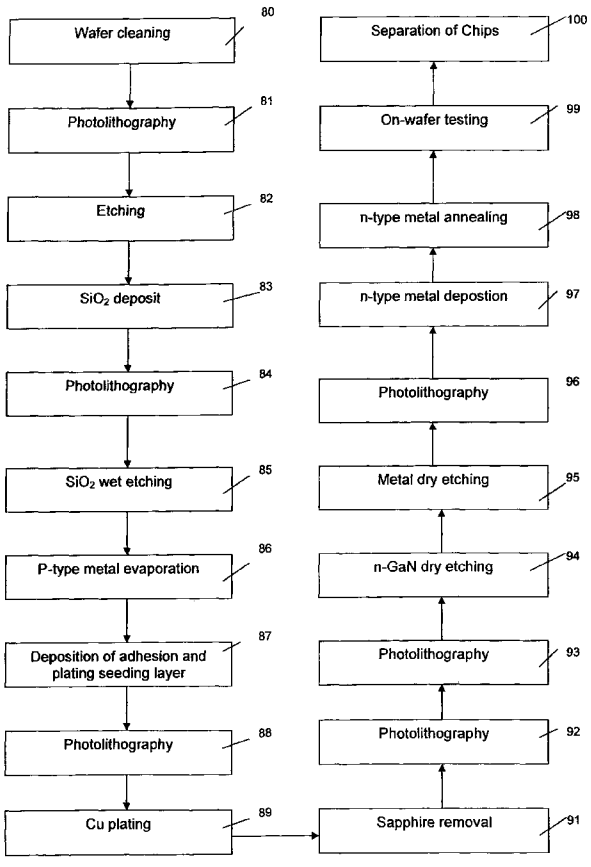
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(54) Title: FABRICATION OF REFLECTIVE LAYER ON SEMICONDUCTOR LIGHT EMITTING DIODES



(57) Abstract: Fabrication of Reflective Layer on Semiconductor Light emitting diodes A method for fabrication of a reflective layer on a semiconductor light emitting diode, the semiconductor light emitting diode having a wafer with multiple epitaxial layers on a substrate; the method comprising applying a first ohmic contact layer on a front surface of the multiple epitaxial layers, the first ohmic contact layer being of a reflective material to also act as a reflective layer.

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